



566.38683CX1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: YOSHIDA, et al

Serial No.: 10/042,271

Filed: January 11, 2002

For: ABRASIVE METHOD OF POLISHING TARGET MEMBER AND
PROCESS FOR PRODUCING SEMICONDUCTOR DEVICE

Group (anticipated): 3723

Examiner (anticipated): D. Nguyen

SUPPLEMENTAL PRELIMINARY AMENDMENT

Assistant Commissioner of Patents
Washington, D.C. 20231

January 25, 2002

Sir:

Supplemental to the Preliminary Amendment filed on
January 11, 2002, please amend the application as follows:

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IN THE CLAIMS

JUN 07 2004

Please cancel Claims 1, 26 and 29.

TECHNOLOGY CENTER R3700

Please add the following new Claims 30 - 49:

--30. An abrasive comprising cerium oxide particles, said
particles having a crystal grain boundary and having a maximum